

STTH16003

High frequency secondary rectifier

Features

- Combines highest recovery and reverse voltage performance
- Ultra-fast, soft and noise-free recovery
- Insulated package: ISOTOP
 - insulated voltage: 2500 V rms
 - capacitance: < 45 pF
- Low inductance and low capacitance allow simplified layout

Description

Dual rectifiers suited for switch mode power supply and high frequency DC to DC converters.

Packaged in ISOTOP, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipment and telecom power supplies.

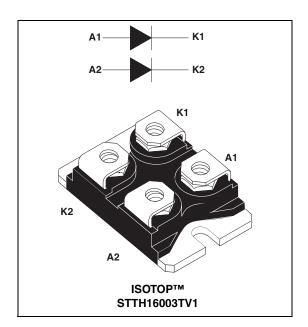


Table 1. Device summary

I _{F(AV)}	2 x 60 A
V_{RRM}	300 V
T _j	150 °C
V _F (typ)	0.95 V
t _{rr} (typ)	80 ns

TM: ISOTOP is a registered trademark of STMicroelectronics

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Characteristics STTH16003

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, $T_{amb} = 25$ °C unless otherwise stated)

Symbol	Parame	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			300	V
I _{F(RMS)}	RMS forward current	RMS forward current			
I _{F(AV)}	Average forward current	$Tc = 85^{\circ}C \delta = 0.5$ Per diode Per device		60 160	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			800	Α
I _{RSM}	Non repetitive peak reverse current $t_p = 100 \mu s square$			5	Α
T _{stg}	Storage temperature range	-55 to + 150	°C		
Tj	Maximum operating junction temperature			150	°C

Table 3. Thermal parameters

Symbol	Parameter Maximum			
D.	Junction to case	Per diode	0.7	
$R_{th(j-c)}$	Total	Total	0.4	°C/W
R _{th(c)}	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} x R_{\text{th(j-c) (per diode)}} + P_{\text{(diode2)}} x R_{\text{th(c)}}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _B = 300 V			200	μΑ
'R`	Theverse leakage current	T _j = 125 °C	V _R – 300 V		0.2	2	mA
V _E ⁽²⁾	V (2) Forward voltage drap	T _j = 25 °C	I _F = 80 A			1.2	V
V _F ⁽²⁾ Forward voltage drop	T _j = 125 °C	1F = 00 A		0.8	0.95	V	

^{1.} Pulse test: t_p = 5 ms, δ < 2 %

^{2.} Pulse test: t_p = 380 μ s, δ < 2 %

^{1.} to evaluate the maximum conduction losses use the following equation: P = 0.75 x $I_{F(AV)}$ + 0.0025 $I_{F}^{2}(RMS)$

STTH16003 Characteristics

Table 5. Recovery characteristics

Symbol	Parameter	Test conditions			Тур	Max.	Unit
	Dovorco roccycry time	T _i = 25 °C	I _F = 0.5 A, I _{rr} = 0.25 A I _R = 1 A			60	ns
t _{rr}	Reverse recovery time	1 _j = 25 C	$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V}$			80	ns
t _{fr}	Forward recovery time	T 05 °C	I _F = 80 A dI _F /dt = 200 A/μs			1000	ns
V _{FP}	Forward recovery voltage	$T_j = 25 {}^{\circ}\text{C}$ $I_F = 80 \text{A}$ $dI_F/dt = 200 \text{A}/\mu \text{s}$ $V_{FR} = 1.1 \text{x} V_{Fmax}$				5	V
I _{RM}	Reverse recovery current	T. = 125 °C	$I_F = 60 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_{cc} = 200 \text{ V}$			16	Α
S _{factor}		1j - 125 C			0.3		-

Figure 1. Conduction losses versus average current (per diode)

Figure 2. Forward voltage drop versus forward current (maximum values, per diode)

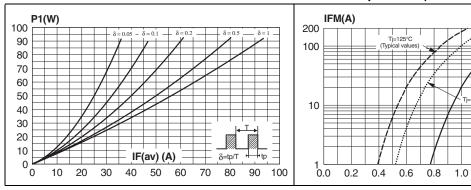
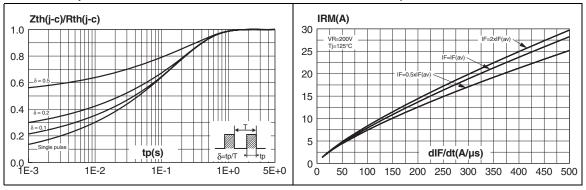


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (90% confidence, per diode)

VFM(V)

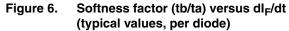
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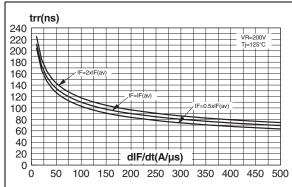


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Characteristics STTH16003

Figure 5. Reverse recovery time versus dI_F/dt (90% confidence, per diode)





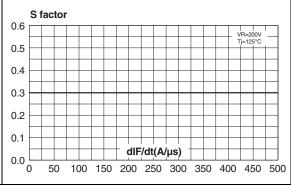
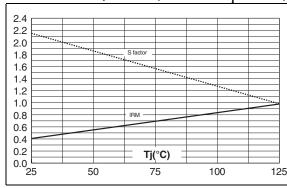


Figure 7. Relative variation of dynamic parameters versus junction temperature (reference: T_i = 125°C)

Figure 8. Transient peak forward voltage versus dl_F/dt (90% confidence, per diode)



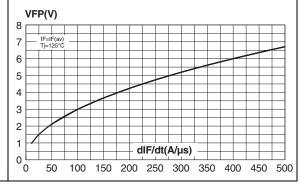
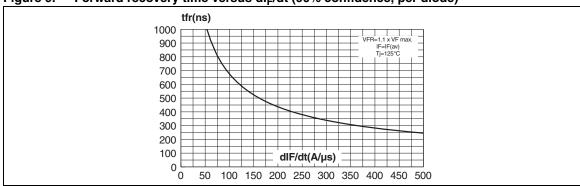


Figure 9. Forward recovery time versus dl_E/dt (90% confidence, per diode)



2 Package information

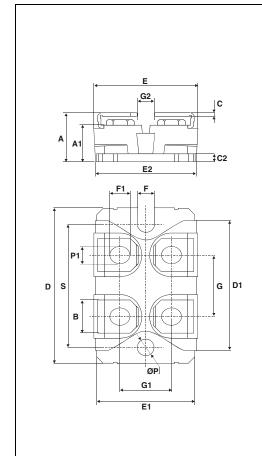
Cooling method: by conduction (C)

Recommended torque value: 0.9 to 1.2 N·m

Epoxy meets UL 94,V0

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at www.st.com.

Table 6. ISOTOP dimensions



	Dimensions				
Ref.	Millim	neters	Inc	hes	
	Min.	Max.	Min.	Max.	
Α	11.80	12.20	0.465	0.480	
A1	8.90	9.10	0.350	0.358	
В	7.8	8.20	0.307	0.323	
С	0.75	0.85	0.030	0.033	
C2	1.95	2.05	0.077	0.081	
D	37.80	38.20	1.488	1.504	
D1	31.50	31.70	1.240	1.248	
Е	25.15	25.50	0.990	1.004	
E1	23.85	24.15	0.939	0.951	
E2	24.80 typ.		0.97	6 typ.	
G	14.90	15.10	0.587	0.594	
G1	12.60	12.80	0.496	0.504	
G2	3.50	4.30	0.138	0.169	
F	4.10	4.30	0.161	0.169	
F1	4.60	5.00	0.181	0.197	
Р	4.00	4.30	0.157	0.69	
P1	4.00	4.40	0.157	0.173	
S	30.10	30.30	1.185	1.193	

Ordering information STTH16003

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH16003TV1	STTH16003TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Description of changes
Oct-1999	4D	Last issue.
25-Jun-2008	5	Reformatted to current standards. Corrected marking in <i>Table 7</i>

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47/